

## ***Supporting Information***

### **Novel Hexameric Tin Carboxylate Clusters as Efficient Negative-Tone EUV Photoresists: High resolution with Well-Defined Patterns using Low Energy Doses**

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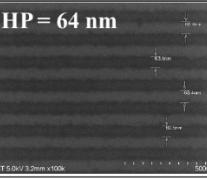
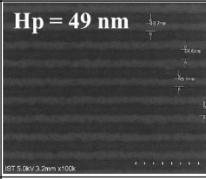
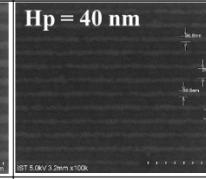
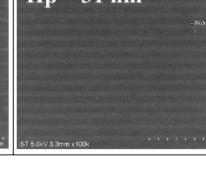
*Po-Wen Chiu<sup>\*b,c</sup> and Rai-Shung Liu<sup>a\*</sup>*

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-----email:rsliu@mx.nthu.edu.tw

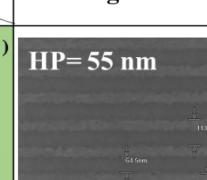
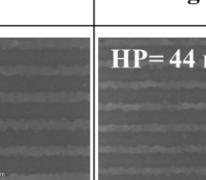
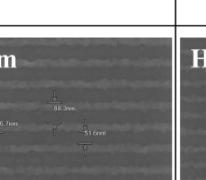
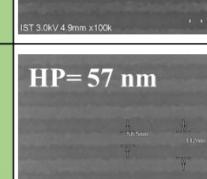
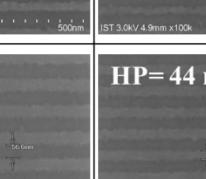
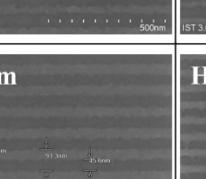
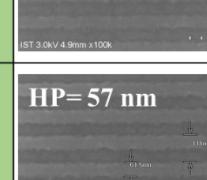
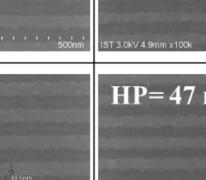
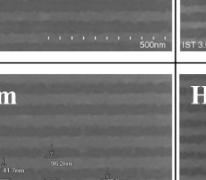
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## 1. SEM image of E-beam lithography patterns

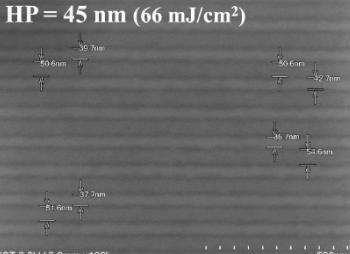
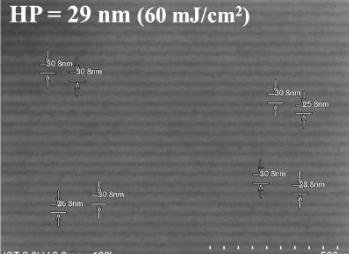
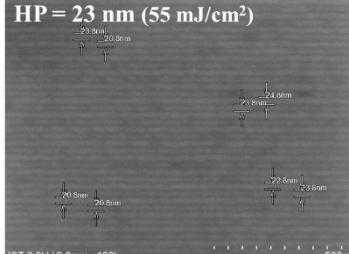
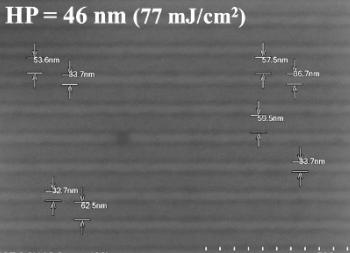
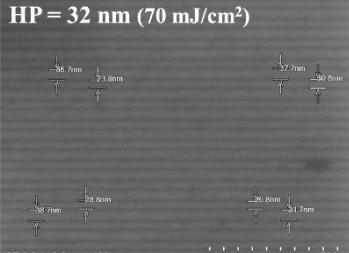
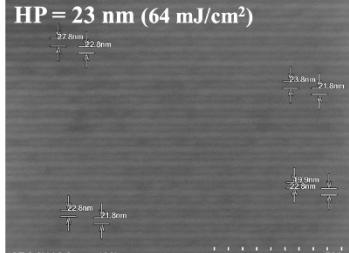
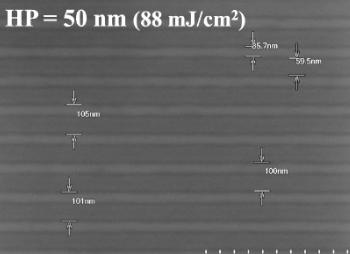
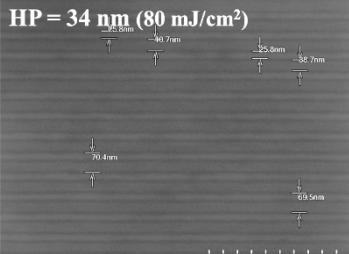
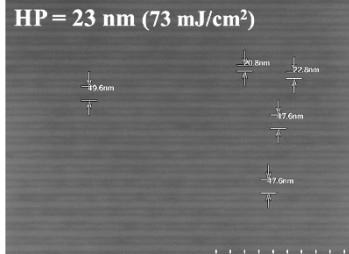
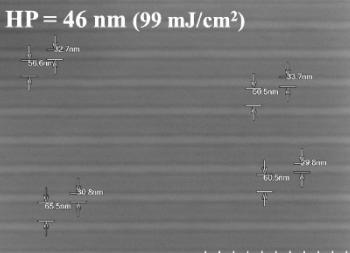
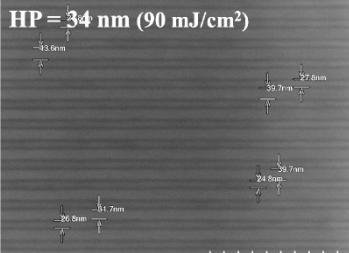
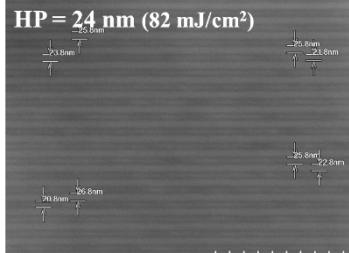
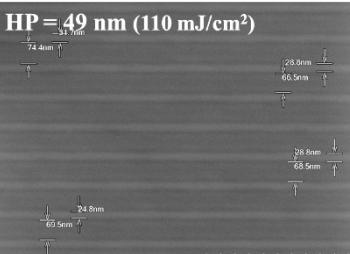
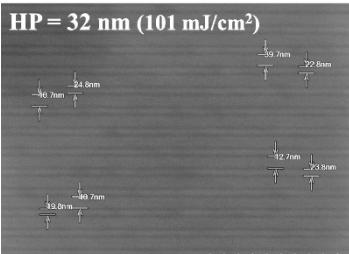
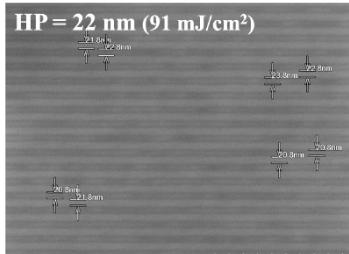
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1120 $\mu\text{C}/\text{cm}^2$ (Design L/S = 1:1.5)	HP = 64 nm 	HP = 49 nm 	HP = 40 nm 	
1440 $\mu\text{C}/\text{cm}^2$ (Design L/S = 1:1)	HP = 52 nm 	HP = 39 nm 	HP = 31 nm 	

**Figure S1.** SEM images of E-beam lithography patterns for cluster 1; Process parameter: 1.5 wt%, THK = 20.9 nm, Developer: 2-Heptanone 60 s, PEB= 80°C 60 s

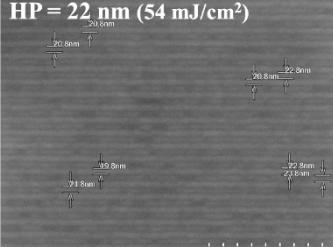
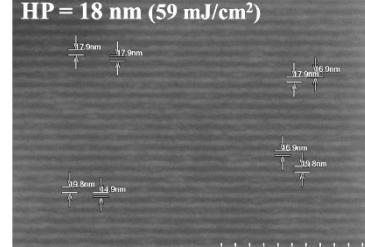
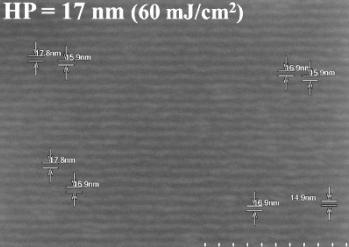
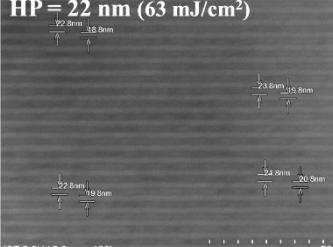
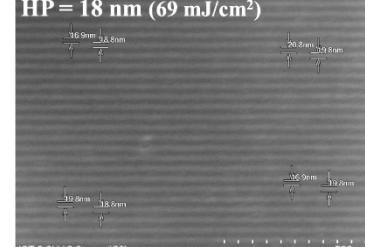
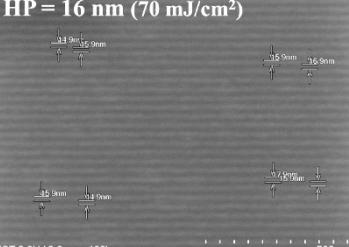
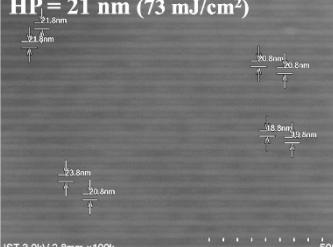
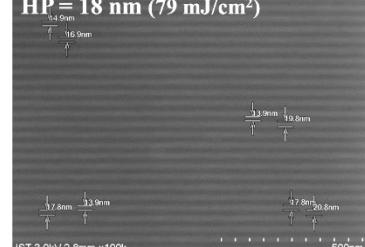
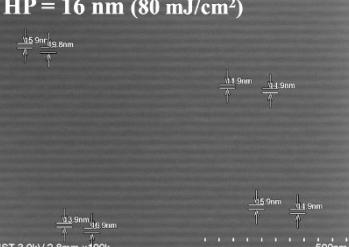
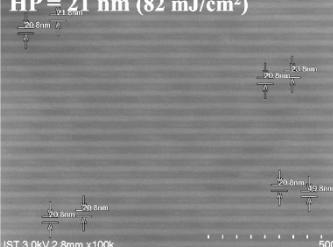
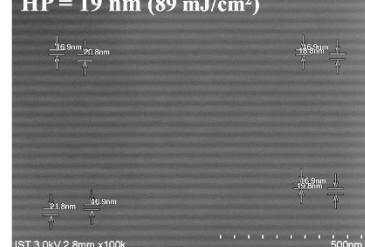
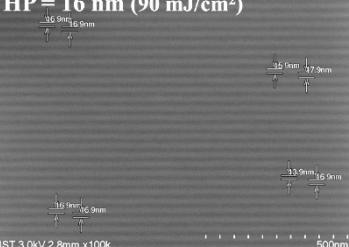
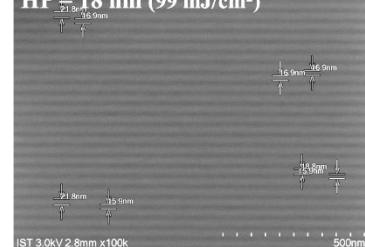
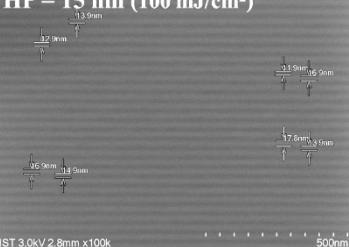
Design HP Dose \	Design HP = 50 nm	Design HP = 40 nm	Design HP = 30 nm
(Design L/S = 1:1.25)	HP= 55 nm 	HP= 44 nm 	HP= 37 nm 
Dose E= 1120 $\mu\text{C}/\text{cm}^2$	HP= 57 nm 	HP= 44 nm 	HP= 35 nm 
Dose E= 1440 $\mu\text{C}/\text{cm}^2$	HP= 57 nm 	HP= 47 nm 	HP= 36 nm 

**Figure S2.** SEM images of E-beam lithography patterns for cluster 2; Process parameter: 1.75 wt%, THK = 22.9 nm, Developer: 2-Heptanone 60 s, PEB = 80°C 60 s

## 2. SEM image of EUV lithography patterns

Design HP= 50 nm	Design HP= 35 nm	Design HP= 25 nm
<b>HP = 45 nm (66 mJ/cm<sup>2</sup>)</b>  IST 3.0kV 2.8mm x100k 500nm	<b>HP = 29 nm (60 mJ/cm<sup>2</sup>)</b>  IST 3.0kV 2.8mm x100k 500nm	<b>HP = 23 nm (55 mJ/cm<sup>2</sup>)</b>  IST 3.0kV 2.9mm x100k 500nm
<b>HP = 46 nm (77 mJ/cm<sup>2</sup>)</b>  IST 3.0kV 2.8mm x100k 500nm	<b>HP = 32 nm (70 mJ/cm<sup>2</sup>)</b>  IST 3.0kV 2.8mm x100k 500nm	<b>HP = 23 nm (64 mJ/cm<sup>2</sup>)</b>  IST 3.0kV 2.8mm x100k 500nm
<b>HP = 50 nm (88 mJ/cm<sup>2</sup>)</b>  IST 3.0kV 2.8mm x100k 500nm	<b>HP = 34 nm (80 mJ/cm<sup>2</sup>)</b>  IST 3.0kV 2.8mm x100k 500nm	<b>HP = 23 nm (73 mJ/cm<sup>2</sup>)</b>  IST 3.0kV 2.8mm x100k 500nm
<b>HP = 46 nm (99 mJ/cm<sup>2</sup>)</b>  IST 3.0kV 2.8mm x100k 500nm	<b>HP = 34 nm (90 mJ/cm<sup>2</sup>)</b>  IST 3.0kV 2.8mm x100k 500nm	<b>HP = 24 nm (82 mJ/cm<sup>2</sup>)</b>  IST 3.0kV 2.8mm x100k 500nm
<b>HP = 49 nm (110 mJ/cm<sup>2</sup>)</b>  IST 3.0kV 2.8mm x100k 500nm	<b>HP = 32 nm (101 mJ/cm<sup>2</sup>)</b>  IST 3.0kV 2.8mm x100k 500nm	<b>HP = 22 nm (91 mJ/cm<sup>2</sup>)</b>  IST 3.0kV 2.8mm x100k 500nm

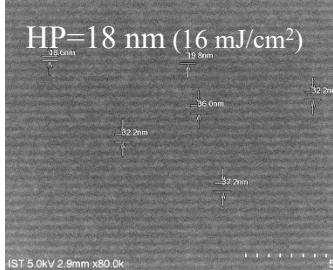
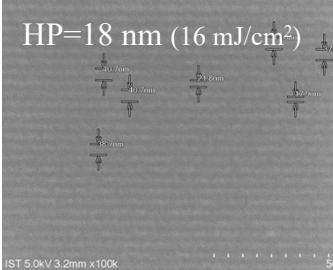
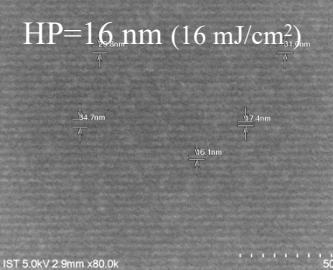
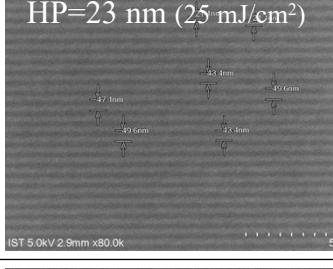
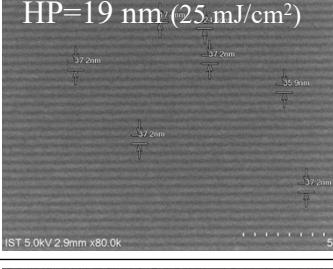
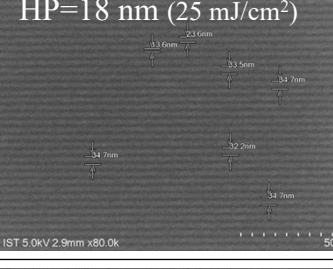
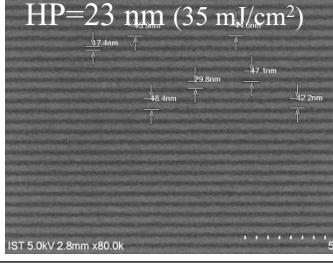
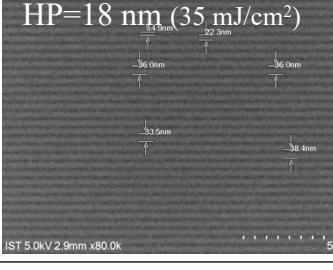
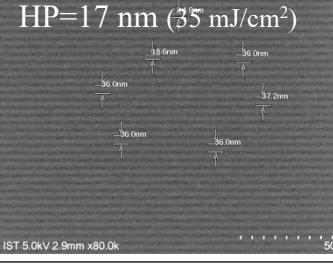
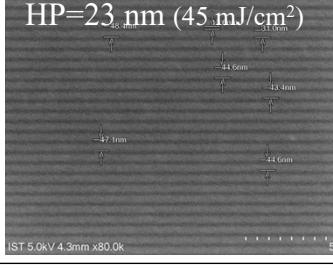
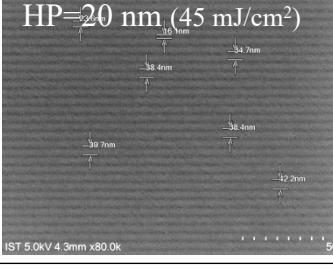
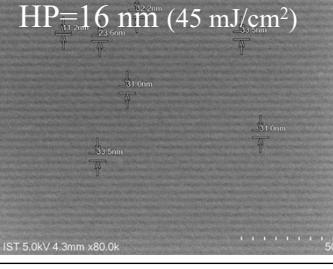
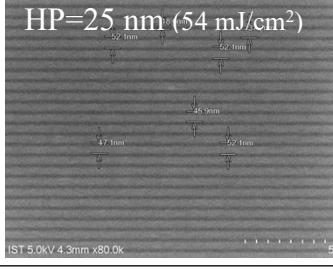
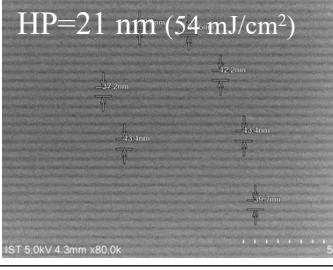
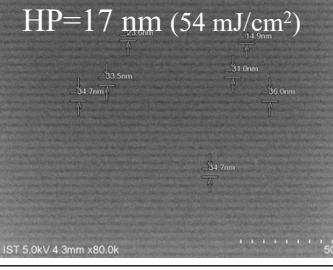
**Figure S3.** SEM images of EUV lithography patterns for cluster 1: HP=50, 35, 25 nm at different dose. Process parameter: 1.5 wt%, THK = 20.9 nm, Developer: 2-Heptanone 60 s, PEB= 80°C 60 s

Design HP= 22 nm	Design HP= 18 nm	Design HP= 16 nm
<b>HP = 22 nm (54 mJ/cm<sup>2</sup>)</b>  IST 3.0kV 2.8mm x100k 500nm	<b>HP = 18 nm (59 mJ/cm<sup>2</sup>)</b>  IST 3.0kV 2.8mm x100k 500nm	<b>HP = 17 nm (60 mJ/cm<sup>2</sup>)</b>  IST 3.0kV 2.9mm x100k 500nm
<b>HP = 22 nm (63 mJ/cm<sup>2</sup>)</b>  IST 3.0kV 2.8mm x100k 500nm	<b>HP = 18 nm (69 mJ/cm<sup>2</sup>)</b>  IST 3.0kV 2.8mm x100k 500nm	<b>HP = 16 nm (70 mJ/cm<sup>2</sup>)</b>  IST 3.0kV 2.8mm x100k 500nm
<b>HP = 21 nm (73 mJ/cm<sup>2</sup>)</b>  IST 3.0kV 2.8mm x100k 500nm	<b>HP = 18 nm (79 mJ/cm<sup>2</sup>)</b>  IST 3.0kV 2.8mm x100k 500nm	<b>HP = 16 nm (80 mJ/cm<sup>2</sup>)</b>  IST 3.0kV 2.8mm x100k 500nm
<b>HP = 21 nm (82 mJ/cm<sup>2</sup>)</b>  IST 3.0kV 2.8mm x100k 500nm	<b>HP = 19 nm (89 mJ/cm<sup>2</sup>)</b>  IST 3.0kV 2.8mm x100k 500nm	<b>HP = 16 nm (90 mJ/cm<sup>2</sup>)</b>  IST 3.0kV 2.8mm x100k 500nm
<b>HP = 22 nm (91 mJ/cm<sup>2</sup>)</b>  IST 3.0kV 2.8mm x100k 500nm	<b>HP = 18 nm (99 mJ/cm<sup>2</sup>)</b>  IST 3.0kV 2.8mm x100k 500nm	<b>HP = 15 nm (100 mJ/cm<sup>2</sup>)</b>  IST 3.0kV 2.8mm x100k 500nm

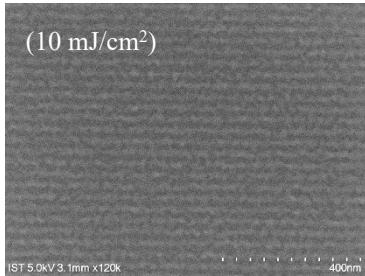
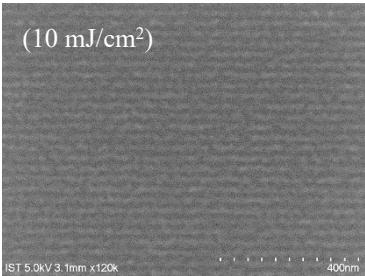
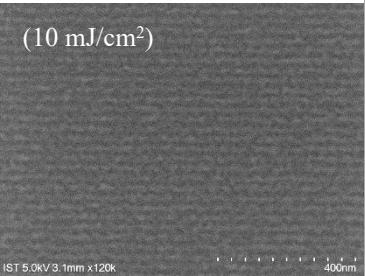
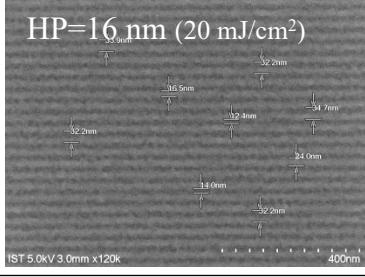
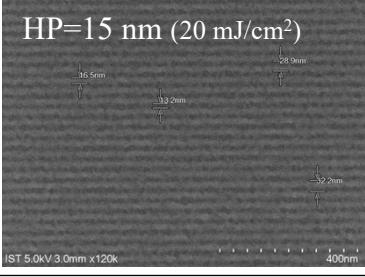
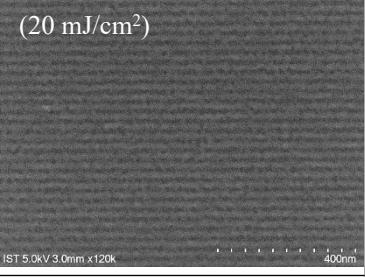
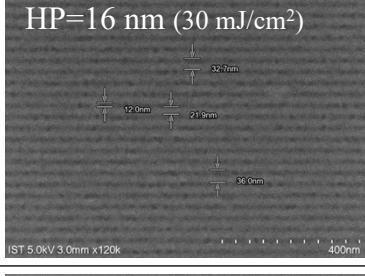
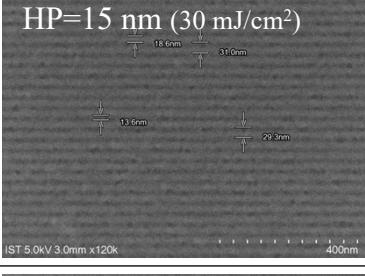
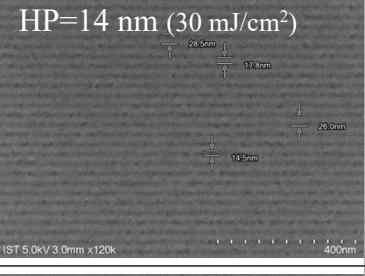
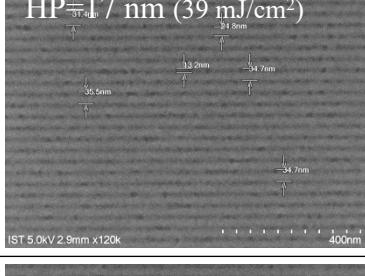
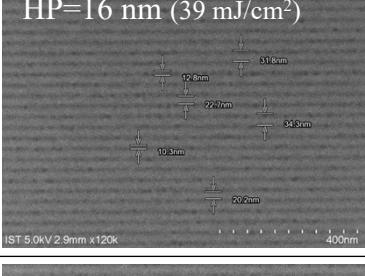
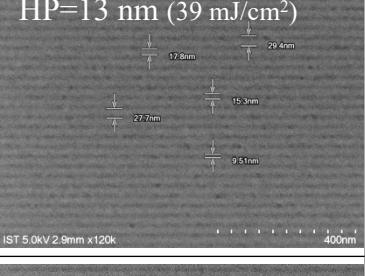
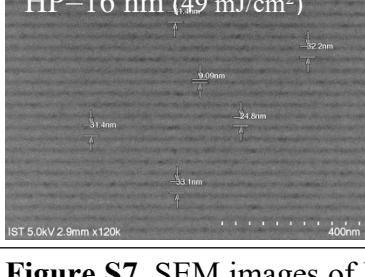
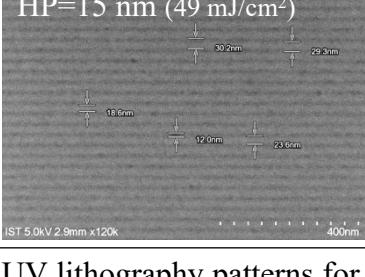
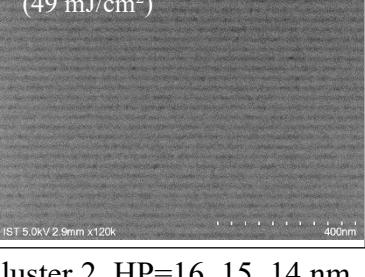
**Figure S4.** SEM images of EUV lithography patterns for cluster 1: HP=22, 18, 16 nm at different dose. Process parameter: 1.5 wt%, THK = 20.9 nm, Developer: 2-Heptanone 60 s, PEB= 80°C 60 s

Design HP= 50 nm	Design HP= 35 nm	Design HP= 25 nm
<p><b>HP=52 nm (16 mJ/cm<sup>2</sup>)</b></p> <p>IST 5.0kV 2.9mm x80.0k      500nm</p>	<p><b>HP=35 nm (16 mJ/cm<sup>2</sup>)</b></p> <p>IST 5.0kV 2.9mm x80.0k      500nm</p>	<p><b>HP=26 nm (16 mJ/cm<sup>2</sup>)</b></p> <p>IST 5.0kV 2.9mm x80.0k      500nm</p>
<p><b>HP=49 nm (25 mJ/cm<sup>2</sup>)</b></p> <p>IST 5.0kV 2.9mm x80.0k      500nm</p>	<p><b>HP=36 nm (25 mJ/cm<sup>2</sup>)</b></p> <p>IST 5.0kV 2.9mm x80.0k      500nm</p>	<p><b>HP=25 nm (25 mJ/cm<sup>2</sup>)</b></p> <p>IST 5.0kV 2.9mm x80.0k      500nm</p>
<p><b>HP=52 nm (35 mJ/cm<sup>2</sup>)</b></p> <p>IST 5.0kV 2.8mm x80.0k      500nm</p>	<p><b>HP=36 nm (35 mJ/cm<sup>2</sup>)</b></p> <p>IST 5.0kV 2.9mm x79.9k      500nm</p>	<p><b>HP=25 nm (35 mJ/cm<sup>2</sup>)</b></p> <p>IST 5.0kV 2.9mm x80.0k      500nm</p>
<p><b>HP=52 nm (45 mJ/cm<sup>2</sup>)</b></p> <p>IST 5.0kV 4.3mm x80.0k      500nm</p>	<p><b>HP=37 nm (45 mJ/cm<sup>2</sup>)</b></p> <p>IST 5.0kV 4.3mm x80.0k      500nm</p>	<p><b>HP=26 nm (45 mJ/cm<sup>2</sup>)</b></p> <p>IST 5.0kV 4.3mm x80.0k      500nm</p>
<p><b>HP=51 nm (54 mJ/cm<sup>2</sup>)</b></p> <p>IST 5.0kV 4.3mm x80.0k      500nm</p>	<p><b>HP=37 nm (54 mJ/cm<sup>2</sup>)</b></p> <p>IST 5.0kV 4.3mm x80.0k      500nm</p>	<p><b>HP=26 nm (54 mJ/cm<sup>2</sup>)</b></p> <p>IST 5.0kV 4.3mm x80.0k      500nm</p>

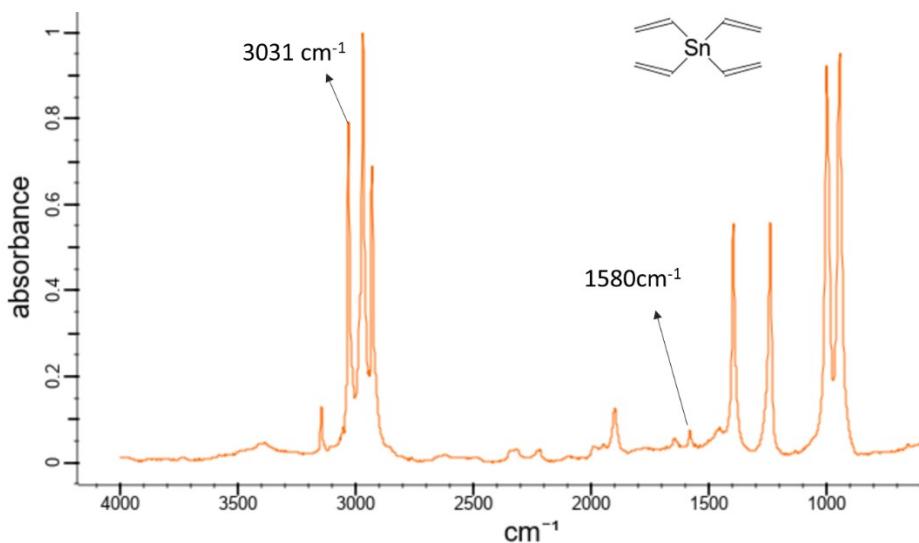
**Figure S5.** SEM images of EUV lithography patterns for cluster 2: HP=50, 35, 25 nm at different dose. Process parameter: 1.75 wt%, PAB = 60°C 60s, THK = 22.9 nm, Developer: 2-Heptanone 60 s, No PEB.

Design HP= 22 nm	Design HP= 18 nm	Design HP= 16 nm
 HP=18 nm (16 mJ/cm <sup>2</sup> ) IST 5.0kV 2.9mm x80.0k 500nm	 HP=18 nm (16 mJ/cm <sup>2</sup> ) IST 5.0kV 3.2mm x100k 500nm	 HP=16 nm (16 mJ/cm <sup>2</sup> ) IST 5.0kV 2.9mm x80.0k 500nm
 HP=23 nm (25 mJ/cm <sup>2</sup> ) IST 5.0kV 2.9mm x80.0k 500nm	 HP=19 nm (25 mJ/cm <sup>2</sup> ) IST 5.0kV 2.9mm x80.0k 500nm	 HP=18 nm (25 mJ/cm <sup>2</sup> ) IST 5.0kV 2.9mm x80.0k 500nm
 HP=23 nm (35 mJ/cm <sup>2</sup> ) IST 5.0kV 2.8mm x80.0k 500nm	 HP=18 nm (35 mJ/cm <sup>2</sup> ) IST 5.0kV 2.9mm x80.0k 500nm	 HP=17 nm (35 mJ/cm <sup>2</sup> ) IST 5.0kV 2.9mm x80.0k 500nm
 HP=23 nm (45 mJ/cm <sup>2</sup> ) IST 5.0kV 4.3mm x80.0k 500nm	 HP=20 nm (45 mJ/cm <sup>2</sup> ) IST 5.0kV 4.3mm x80.0k 500nm	 HP=16 nm (45 mJ/cm <sup>2</sup> ) IST 5.0kV 4.3mm x80.0k 500nm
 HP=25 nm (54 mJ/cm <sup>2</sup> ) IST 5.0kV 4.3mm x80.0k 500nm	 HP=21 nm (54 mJ/cm <sup>2</sup> ) IST 5.0kV 4.3mm x80.0k 500nm	 HP=17 nm (54 mJ/cm <sup>2</sup> ) IST 5.0kV 4.3mm x80.0k 500nm

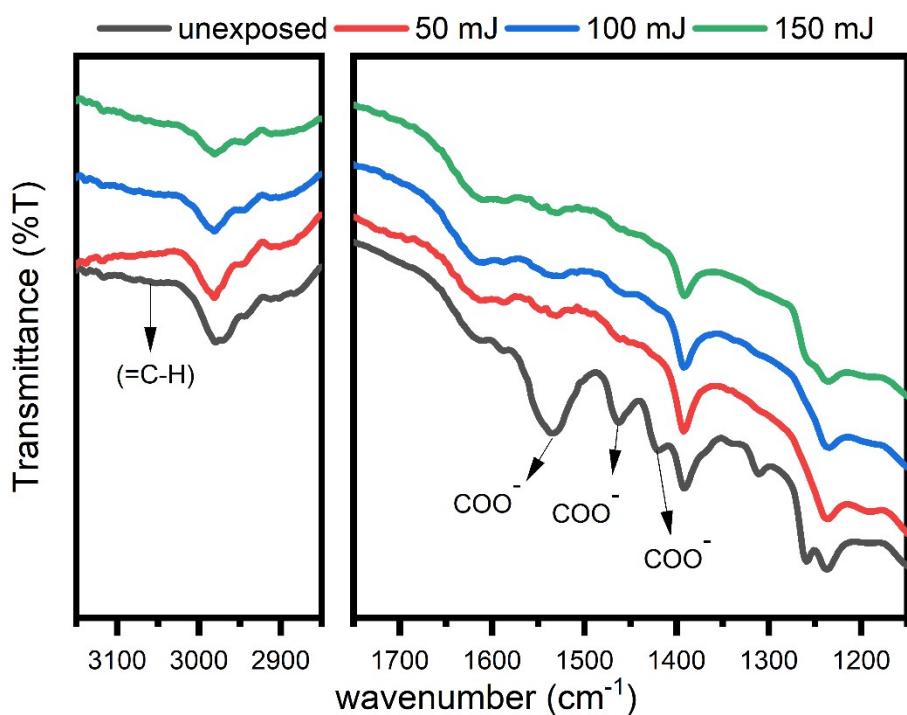
**Figure S6.** SEM images of EUV lithography patterns for cluster 2. HP=22, 18, 16 nm at different dose. Process parameter: 1.75 wt%, PAB = 60°C 60s, THK = 22.9 nm, Developer: 2-Heptanone 60 s, No PEB.

Design HP= 16 nm	Design HP= 15 nm	Design HP= 14 nm
(10 mJ/cm <sup>2</sup> )  IST 5.0kV 3.1mm x120k 400nm	(10 mJ/cm <sup>2</sup> )  IST 5.0kV 3.1mm x120k 400nm	(10 mJ/cm <sup>2</sup> )  IST 5.0kV 3.1mm x120k 400nm
HP=16 nm (20 mJ/cm <sup>2</sup> )  IST 5.0kV 3.0mm x120k 400nm	HP=15 nm (20 mJ/cm <sup>2</sup> )  IST 5.0kV 3.0mm x120k 400nm	(20 mJ/cm <sup>2</sup> )  IST 5.0kV 3.0mm x120k 400nm
HP=16 nm (30 mJ/cm <sup>2</sup> )  IST 5.0kV 3.0mm x120k 400nm	HP=15 nm (30 mJ/cm <sup>2</sup> )  IST 5.0kV 3.0mm x120k 400nm	HP=14 nm (30 mJ/cm <sup>2</sup> )  IST 5.0kV 3.0mm x120k 400nm
HP=17 nm (39 mJ/cm <sup>2</sup> )  IST 5.0kV 2.9mm x120k 400nm	HP=16 nm (39 mJ/cm <sup>2</sup> )  IST 5.0kV 2.9mm x120k 400nm	HP=13 nm (39 mJ/cm <sup>2</sup> )  IST 5.0kV 2.9mm x120k 400nm
HP=16 nm (49 mJ/cm <sup>2</sup> )  IST 5.0kV 2.9mm x120k 400nm	HP=15 nm (49 mJ/cm <sup>2</sup> )  IST 5.0kV 2.9mm x120k 400nm	(49 mJ/cm <sup>2</sup> )  IST 5.0kV 2.9mm x120k 400nm

**Figure S7.** SEM images of EUV lithography patterns for cluster 2, HP=16, 15, 14 nm at different dose. Process parameter: 1.75 wt%, PAB = 60°C 40s, THK = 20.62 nm, Developer: 2-Heptanone 60 s, No PEB.



**Figure S8.** IR spectra of  $\text{Sn}(\text{vinyl})_4$



**Figure S9.** Spectra of photoresist 2 in which the two regions are plotted on equal Magnitudes.

**3. Table S1. LWR values for cluster 1 :**

Cluster 1 HP = 18 nm	
Dose (mJ/cm <sup>2</sup> )	LWR (nm)
79	4.6
89	4.9
99	5.2

The computation is based on a software: see: I. Mochi, M. Vockenhuber, T. Allenet, Y. Ekinci, *Proc. SPIE*, 2021, **11855**, 1185502

#### 4. X-ray crystallographic structures and data

##### 4.1 Crystal data and X-ray structure of cluster 1 :

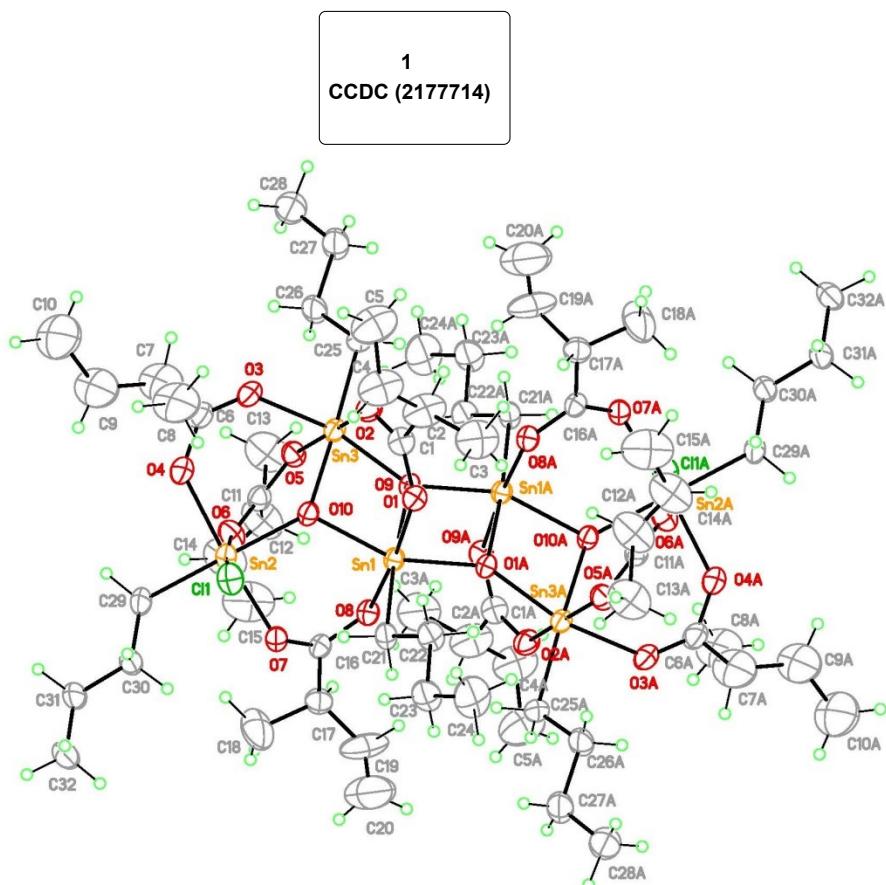


Table 1 Crystal data and structure refinement for 220347lt\_auto.

Identification code	220347lt_auto
Empirical formula	C <sub>32</sub> H <sub>55</sub> ClO <sub>10</sub> Sn <sub>3</sub>
Formula weight	991.28
Temperature/K	99.99(10)
Crystal system	triclinic

Space group	P-1
a/Å	12.4749(4)
b/Å	12.5391(3)
c/Å	15.0700(4)
$\alpha/^\circ$	90.977(2)
$\beta/^\circ$	104.825(3)
$\gamma/^\circ$	117.675(3)
Volume/Å <sup>3</sup>	1992.54(11)
Z	2
$\rho_{\text{calc}} \text{g/cm}^3$	1.652
$\mu/\text{mm}^{-1}$	15.858
F(000)	988.0
Crystal size/mm <sup>3</sup>	0.21 × 0.14 × 0.06
Radiation	Cu K $\alpha$ ( $\lambda = 1.54184$ )
2 $\Theta$ range for data collection/°	6.144 to 145.92
Index ranges	-15 ≤ h ≤ 14, -13 ≤ k ≤ 15, -18 ≤ l ≤ 18
Reflections collected	26569
Independent reflections	7521 [ $R_{\text{int}} = 0.0478$ , $R_{\text{sigma}} = 0.0387$ ]
Data/restraints/parameters	7521/317/536
Goodness-of-fit on F <sup>2</sup>	1.273
Final R indexes [I>=2σ (I)]	$R_1 = 0.0592$ , wR <sub>2</sub> = 0.1713
Final R indexes [all data]	$R_1 = 0.0678$ , wR <sub>2</sub> = 0.1778
Largest diff. peak/hole / e Å <sup>-3</sup>	1.63/-1.52

### 4.3 Crystal data and X-ray structure of cluster 2 :

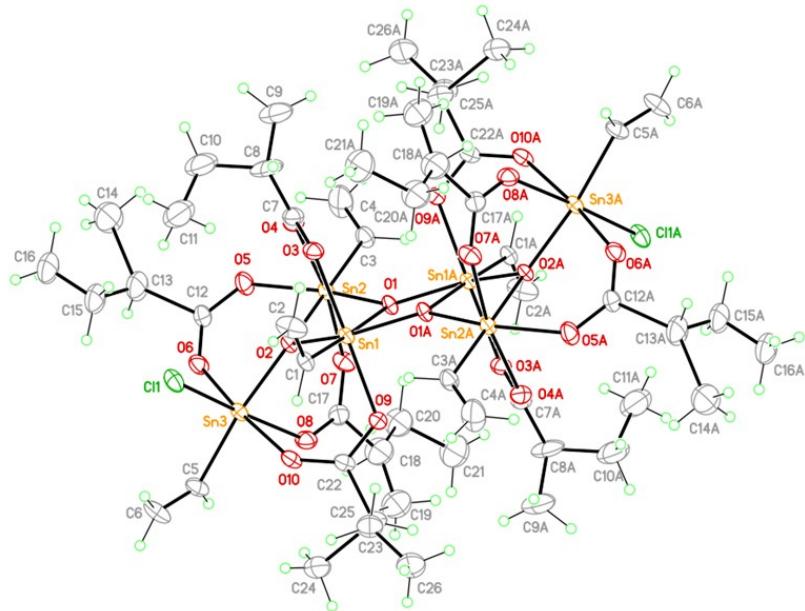


Table 1. Crystal data and structure refinement for 210753lt\_0m\_a.

Identification code	210753lt_0m_a		
Empirical formula	C <sub>52</sub> H <sub>90</sub> Cl <sub>2</sub> O <sub>20</sub> Sn <sub>6</sub>		
Formula weight	1818.27		
Temperature	100(2) K		
Wavelength	0.71073 Å		
Crystal system	Triclinic		
Space group	P-1		
Unit cell dimensions	a = 10.7499(9) Å	α = 67.810(4)°.	
	b = 13.2738(11) Å	β = 71.148(4)°.	
	c = 14.0693(11) Å	γ = 73.030(4)°.	
Volume	1725.8(3) Å <sup>3</sup>		
Z	1		
Density (calculated)	1.750 Mg/m <sup>3</sup>		
Absorption coefficient	2.278 mm <sup>-1</sup>		
F(000)	896		
Crystal size	0.23 x 0.20 x 0.06 mm <sup>3</sup>		
Theta range for data collection	1.610 to 26.514°.		
Index ranges	-13<=h<=12, -16<=k<=16, -17<=l<=16		
Reflections collected	28957		
Independent reflections	7053 [R(int) = 0.0502]		
Completeness to theta = 25.242°	99.6 %		

Absorption correction	Semi-empirical from equivalents
Max. and min. transmission	0.7454 and 0.6419
Refinement method	Full-matrix least-squares on F <sup>2</sup>
Data / restraints / parameters	7053 / 414 / 525
Goodness-of-fit on F <sup>2</sup>	1.080
Final R indices [I>2sigma(I)]	R1 = 0.0406, wR2 = 0.1111
R indices (all data)	R1 = 0.0539, wR2 = 0.1288
Extinction coefficient	n/a
Largest diff. peak and hole	1.401 and -1.066 e.Å <sup>-3</sup>



## **5. Spectral data of key compounds**

### **5.1 Spectral data for cluster 1 :**

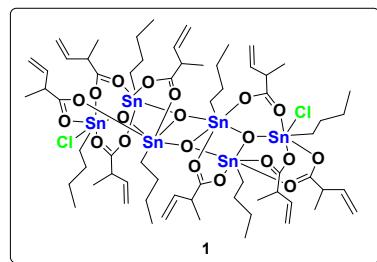
Transparent crystal (59%) ;  $^1\text{H}$  NMR (400 MHz,  $\text{CDCl}_3$ ) :  $\delta$  5.92-5.88 (m, 8H), 5.12-5.07 (m, 16H), 3.12-3.04 (m, 8H), 1.73-1.62 (m, 24H), 1.34-1.32 (m, 12H), 1.24-1.18 (m, 24H), 0.88 (d,  $J = 7.1$  Hz, 18H);  $^{13}\text{C}$  NMR (125 MHz,  $\text{CDCl}_3$ ) :  $\delta$  182.7, 181.8, 138.7, 137.9, 137.7, 115.8, 115.4, 115.1, 114.9, 114.5, 114.4, 46.5, 46.5, 46.3, 46.2, 35.6, 35.5, 27.7, 27.5, 27.2, 27.1, 26.7, 26.4, 26.2, 26.1, 25.7, 17.2, 17.0;  $^{119}\text{Sn}$  NMR (186 MHz,  $\text{CDCl}_3$ ) :  $\delta$  -483.9, -522.3, -523.6, -551.1; HRMS (ESI+, m/z) Calcd. For  $^{12}\text{C}_{64}\text{H}_{110}^{35}\text{Cl}_2\text{O}_{20}^{120}\text{Sn}_6 [\text{M}+\text{H}]^+$  : 1989.11, found : 1989.87; EA Anal. Calcd. for  $\text{C}_{64}\text{H}_{110}\text{Cl}_2\text{O}_{20}\text{Sn}_6$  : C : 38.77% ; H : 5.59%, found : C : 38.65% ; H : 5.58%.

### **5.2 Spectral data for cluster 2 :**

Transparent crystal (65%);  $^1\text{H}$  NMR (500 MHz,  $\text{CDCl}_3$ ) :  $\delta$  6.22-5.91 (m, 18H), 2.44-2.24 (m, 8H), 1.72-1.35 (m, 16H), 1.17-1.07 (m, 24H), 0.93-0.85 (m, 24H) ;  $^{13}\text{C}$  NMR (125 MHz,  $\text{CDCl}_3$ ) :  $\delta$  186.0, 185.4, 185.2, 185.1, 184.6, 184.1, 183.5, 145.2, 141.9, 141.1, 140.8, 139.7, 139.3, 138.7, 138.3, 138.1, 136.3, 135.5, 135.1, 134.5, 133.9, 133.5, 133.0, 132.1, 131.8, 131.2, 123.0, 43.9, 43.8, 43.8, 43.6, 40.5, 27.3, 27.2, 27.1, 26.8, 16.9, 16.8, 16.7, 16.5, 11.7, 11.5;  $^{119}\text{Sn}$  NMR (186 MHz,  $\text{CDCl}_3$ ) :  $\delta$  -183.96, -539.25, -542.63, -547.88. HRMS (ESI+, m/z) Calcd. For  $\text{C}_{52}\text{H}_{90}\text{Cl}_2\text{O}_{20}\text{Sn}_6 [\text{M}+\text{H}]^+$  : 1823.95, found: 1824.75; EA Anal. Calcd. for  $\text{C}_{52}\text{H}_{90}\text{Cl}_2\text{O}_{20}\text{Sn}_6$ : C: 34.35%; H: 4.99%, found: C: 34.32%; H: 4.94%.

## 6. $^1\text{H}$ and $^{13}\text{C}$ NMR of key compounds

### 6.1 Spectral data for cluster 1



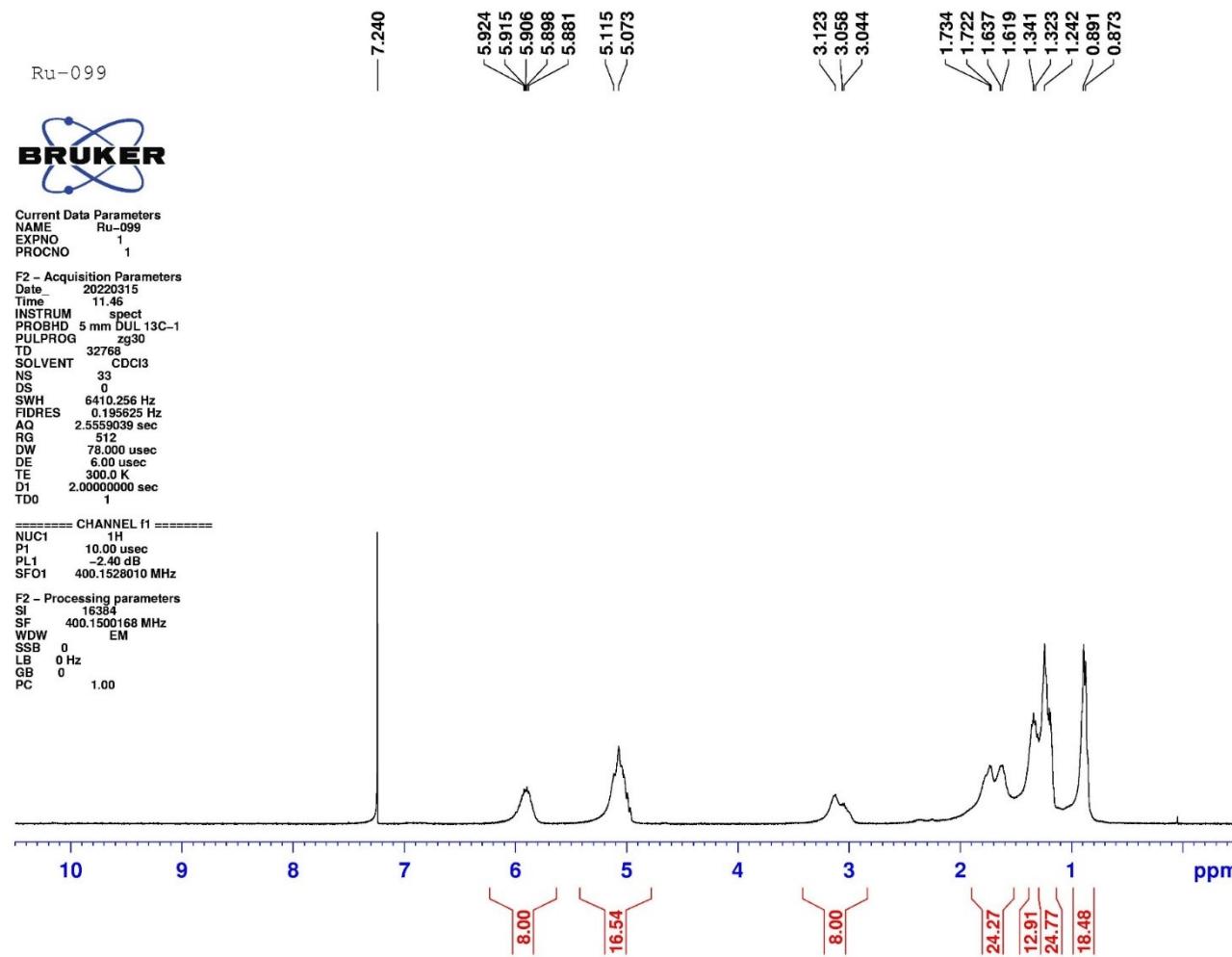
Ru-099  
**BRUKER**

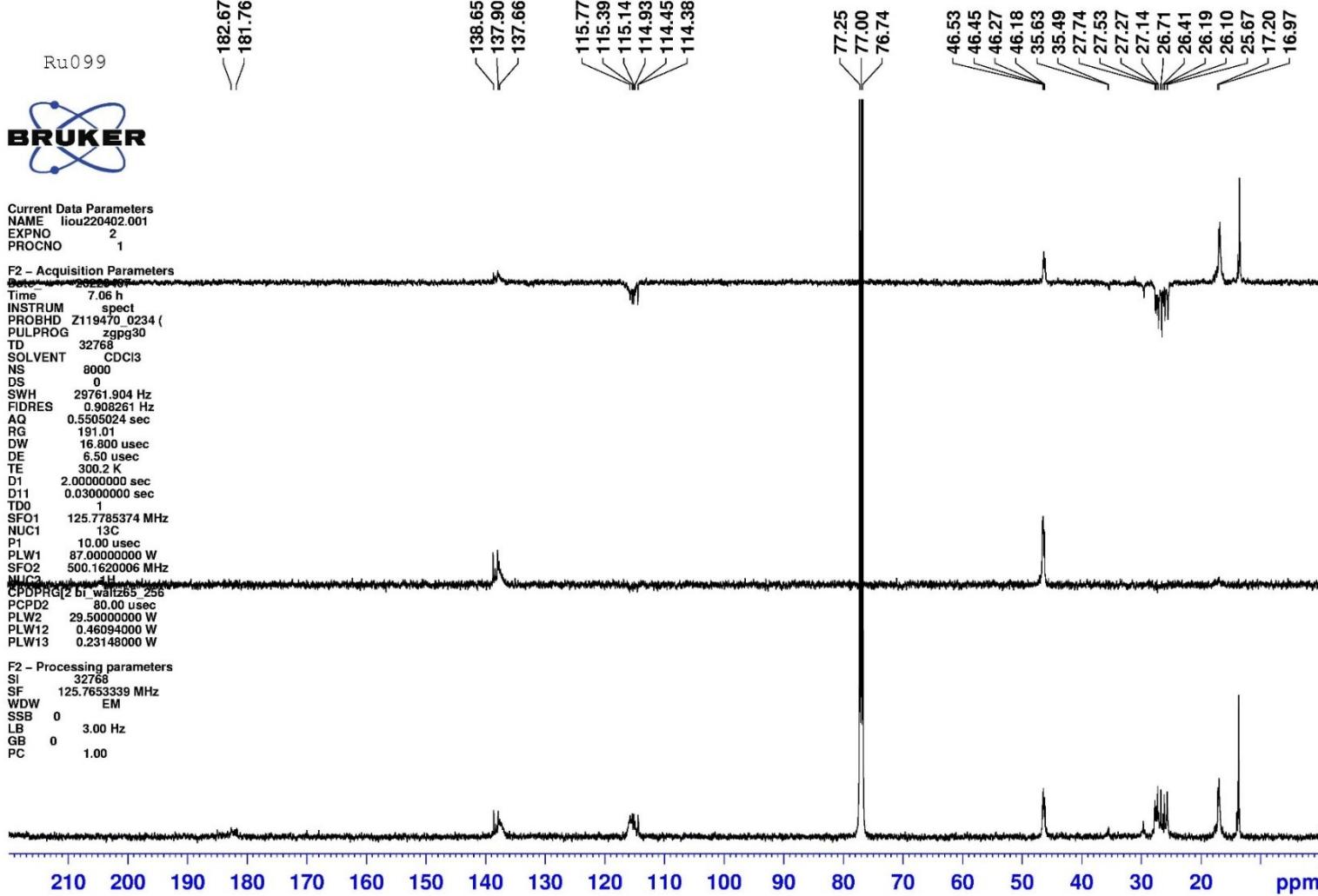
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 TD 32768  
 SOLVENT CDCl<sub>3</sub>  
 NS 33  
 DS 0  
 SWH 6410.256 Hz  
 FIDRES 0.195925 Hz  
 AQ 2.5550239 sec  
 RG 512  
 DW 78.000 usec  
 DE 6.00 usec  
 TE 300.0 K  
 D1 2.0000000 sec  
 TDO 1

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 P1 10.00 usec  
 PL1 -2.40 dB  
 SFO1 400.1528010 MHz

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 SSB 0  
 LB 0 Hz  
 GB 0  
 PC 1.00







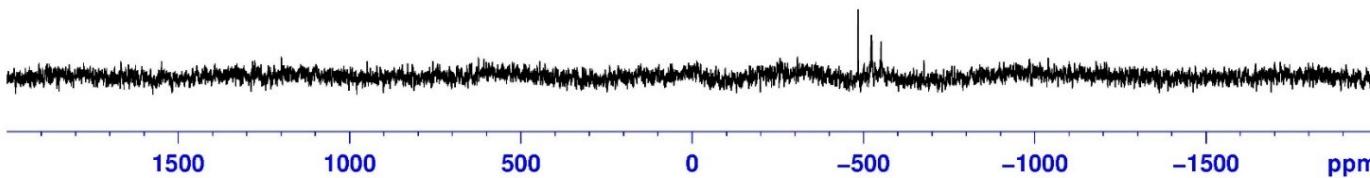
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PROCNO 1

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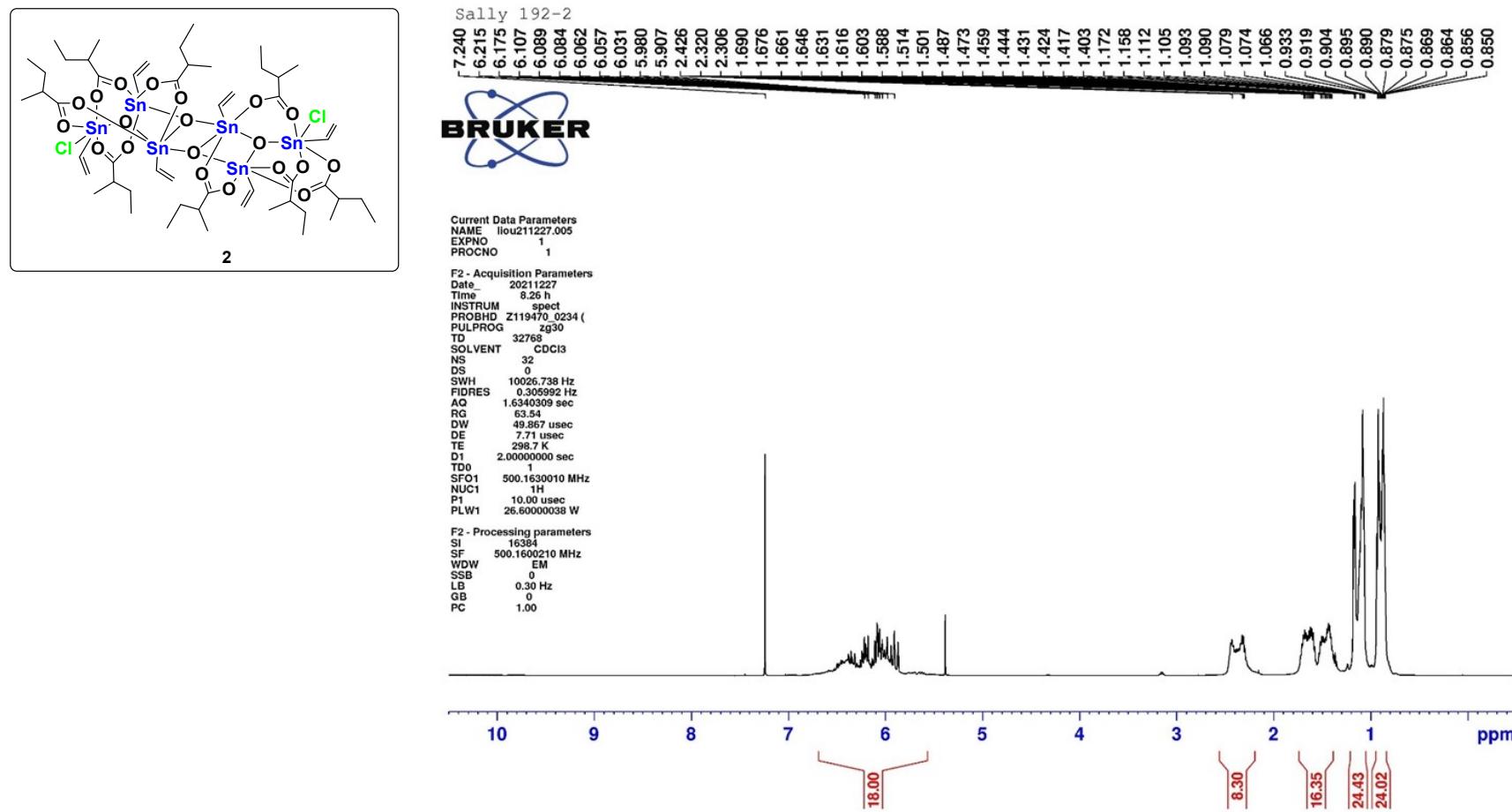
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RG 191.01  
DW 0.667 usec  
DE 6.50 usec  
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D11 0.0300000 sec  
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SFO1 186.5128250 MHz  
NUC1 119Sn  
P1 15.00 usec  
PLW1 50.0000000 W  
SFO2 500.1620006 MHz  
NUC2 1H  
CPDPRG[2 waltz16  
PCPD2 80.00 usec  
PLW2 29.5000000 W  
PLW12 0.46094000 W  
PLW13 0.23148000 W

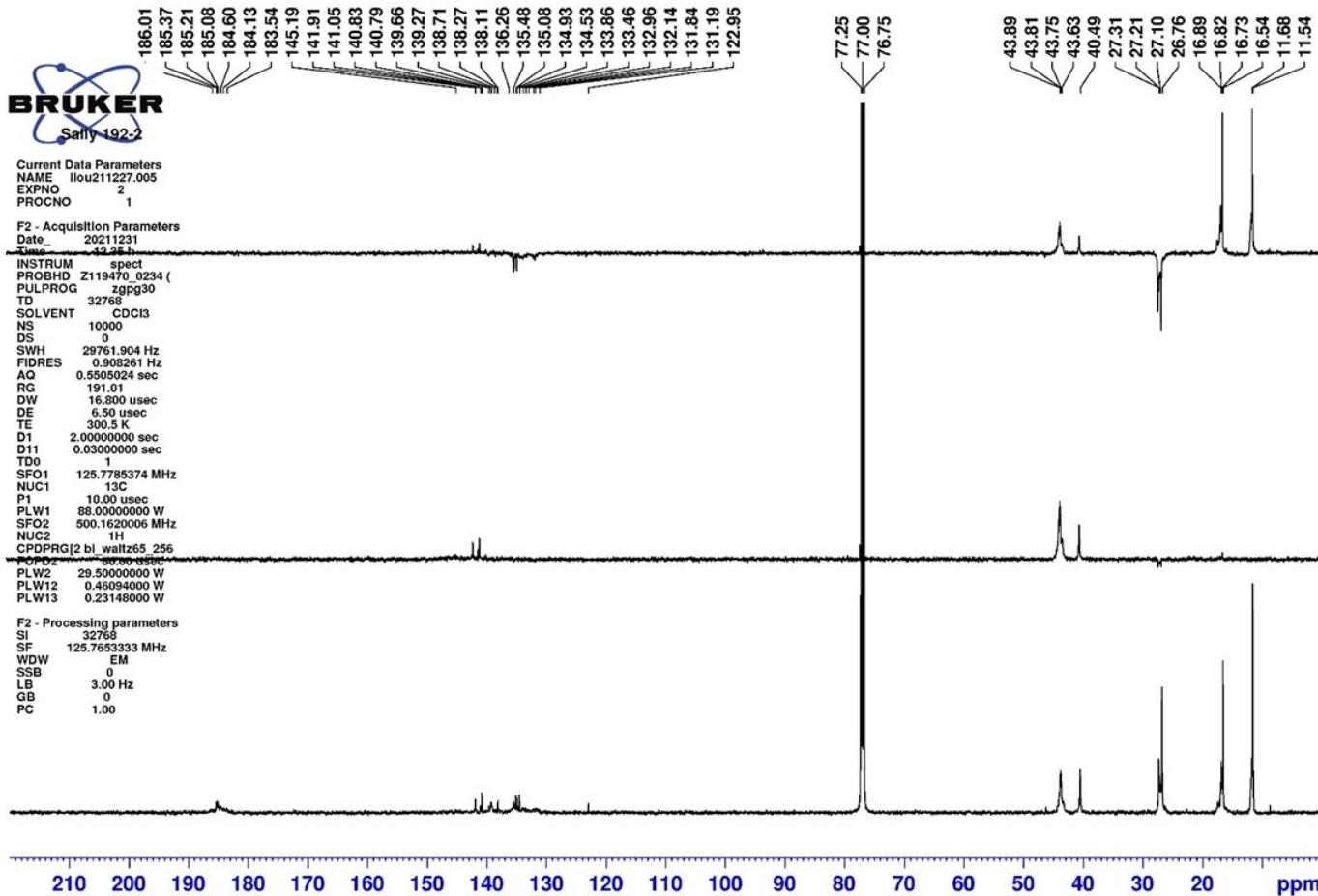
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-522.263  
-523.632  
-551.054



## 6.2 Spectral data for cluster 2







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PROCNO 1

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Date 20211231

Time 19.28 h

INSTRUM spect

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PULPROG zgpg

TD 65536

SOLVENT CDCl3

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DW 0.667 usec

DE 6.50 usec

TE 300.3 K

D1 2.0000000 sec

D11 0.0300000 sec

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NUC1 119Sn

PT 15.00 usec

PLW1 50.00000000 W

SF02 500.1940006 MHz

NUC2 11

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PCRD2 80.00 usec

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PLW12 0.46094000 W

PLW13 0.23148000 W

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SF 186.5128038 MHz

WDW EM

SSB 0

